



Reliability of GaAs Discrete FETs



Figure 1 demonstrates the high temperature DC life test results of Transcom T5 (2.4 mm) GaAs HFET. The devices exhibit an extrapolated DC lifetime of more than 10⁸ hours at 110 °C Channel Temperature. The MTTF test results derived from three elevated channel temperatures of 226 °C, 246 °C and 260 °C. Failure of the devices defined as 20 % degradation in Idss from room temperature values.

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